

Product Summary

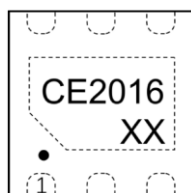
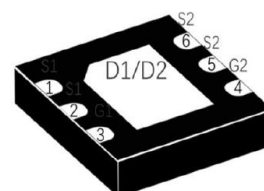
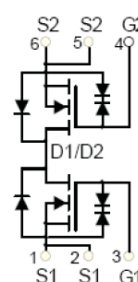
$V_{(BR)DSS}$	$R_{DS(on)TYP}$	I_D
20V	13m Ω @4.5V	7A
	18m Ω @2.5V	

Feature

- Trench Technology Power MOSFET
- Low $R_{DS(ON)}$
- Low Gate Charge
- ESD Protected

Application

- Load Switch
- DC/DC Converter

MARKING:

DFN2X2-6L

Schematic diagram

ABSOLUTE MAXIMUM RATINGS ($T_A = 25^\circ\text{C}$ unless otherwise noted)

Parameter		Symbol	Value	Unit
Drain - Source Voltage		V_{DS}	20	V
Gate - Source Voltage		V_{GS}	± 12	V
Continuous Drain Current ^{1,5}	$T_A = 25^\circ\text{C}$	I_D	7	A
Pulsed Drain Current ²		I_{DM}	28	A
Power Dissipation ^{4,5}	$T_A = 25^\circ\text{C}$	P_D	0.75	W
Thermal Resistance from Junction to Ambient ⁵		$R_{\theta JA}$	167	$^\circ\text{C/W}$
Junction Temperature and Storage Temperature		T_J, T_{STG}	-55~ +150	$^\circ\text{C}$

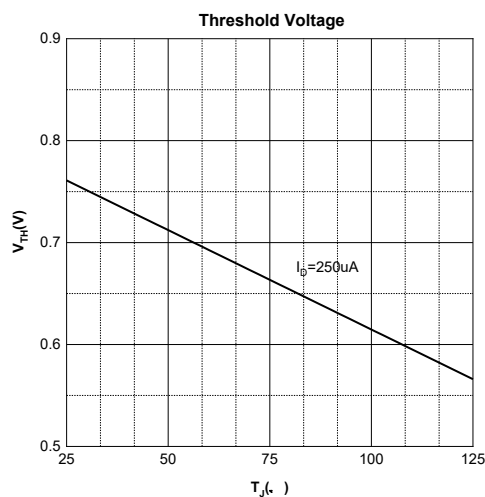
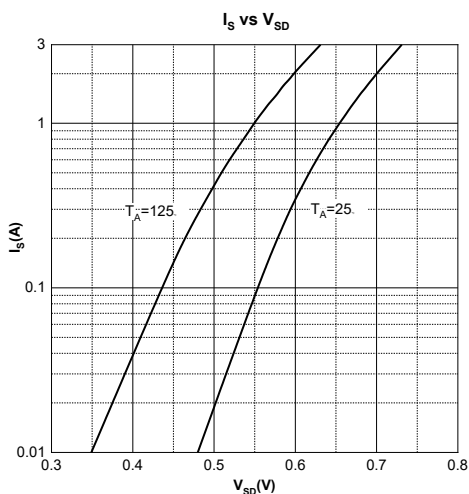
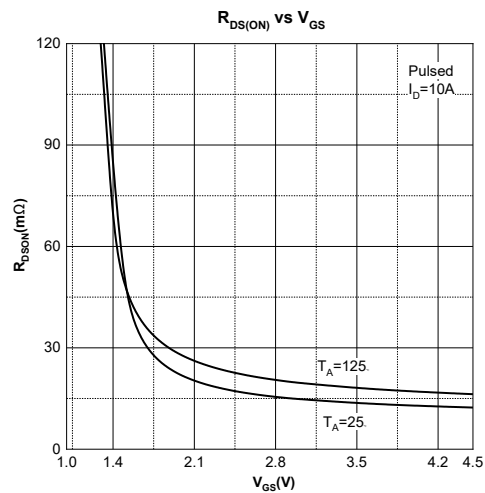
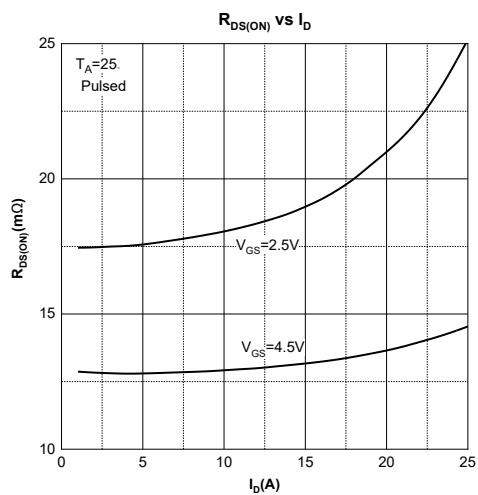
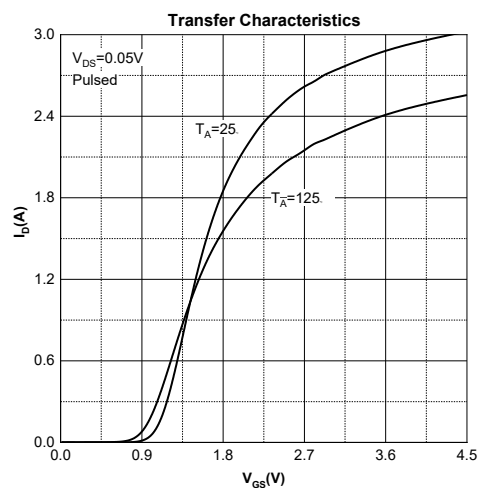
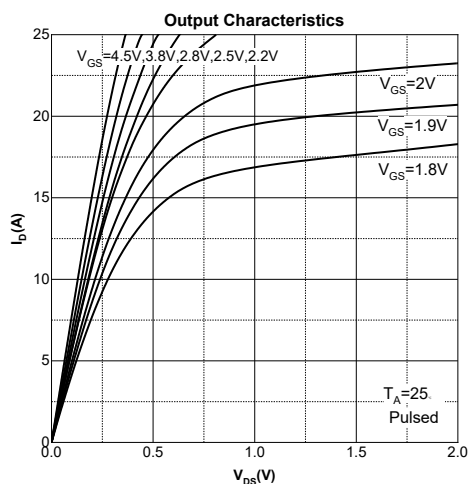
MOSFET ELECTRICAL CHARACTERISTICS ($T_A = 25^\circ\text{C}$ unless otherwise noted)

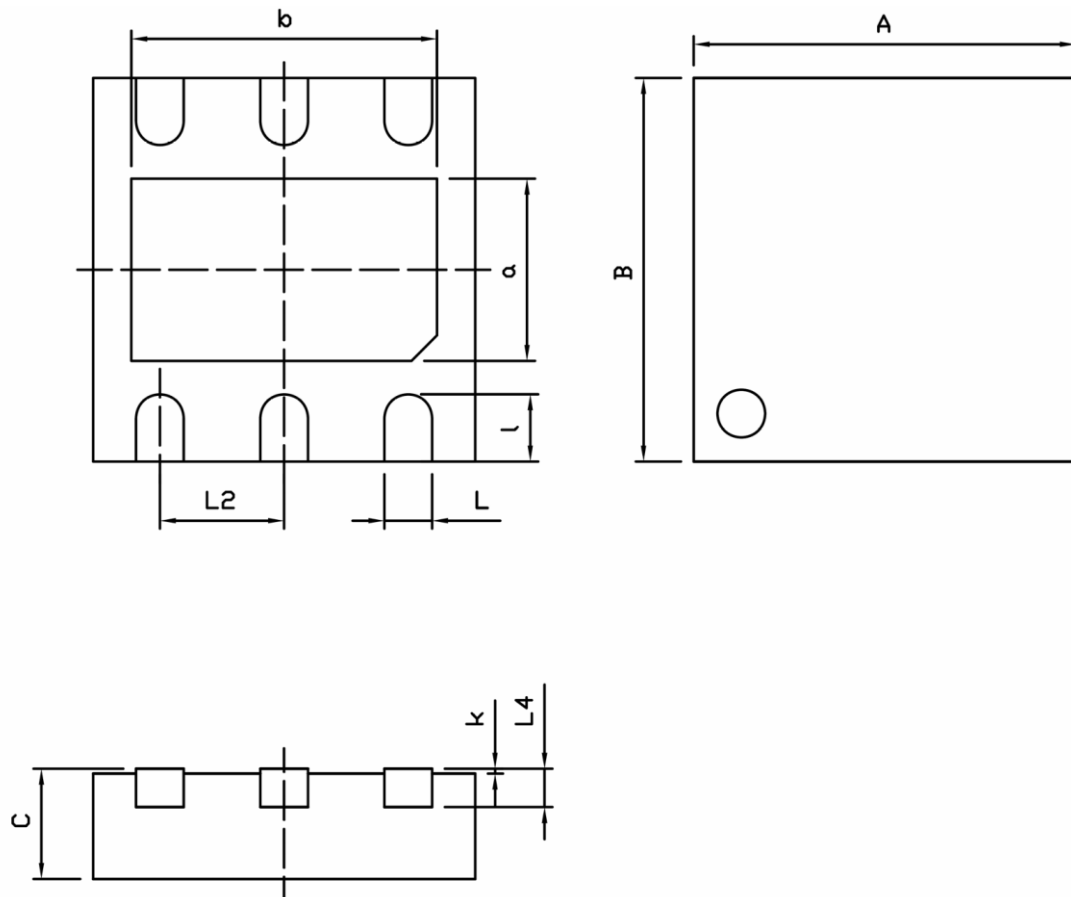
Parameter	Symbol	Test Condition	Min	Type	Max	Unit
Off Characteristics						
Drain - Source Breakdown Voltage	$V_{(BR)DSS}$	$V_{GS} = 0V, I_D = 250\mu A$	20			V
Zero Gate Voltage Drain Current	I_{DSS}	$V_{DS} = 16V, V_{GS} = 0V$			1	μA
Gate - Body Leakage Current	I_{GSS}	$V_{GS} = \pm 10V, V_{DS} = 0V$			± 4	μA
On Characteristics ³						
Gate Threshold Voltage	$V_{GS(th)}$	$V_{DS} = V_{GS}, I_D = 250\mu A$	0.5	0.75	1.1	V
Drain-source On-resistance	$R_{DS(on)}$	$V_{GS} = 4.5V, I_D = 3A$		13	21	m Ω
		$V_{GS} = 2.5V, I_D = 3A$		18	26	
Dynamic Characteristics						
Input Capacitance	C_{iss}	$V_{DS} = 10V, V_{GS} = 0V, f = 0.1MHz$		431.4		pF
Output Capacitance	C_{oss}			107		
Reverse Transfer Capacitance	C_{rss}			36		
Gate Resistance	R_g	$V_{DS} = 0V, V_{GS} = 0V, f = 1MHz$		525		Ω
Switching Characteristics						
Total Gate Charge	Q_g	$V_{DS} = 10V, V_{GS} = 4.5V, I_D = 3A$		7.6		nC
Gate-Source Charge	Q_{gs}			0.5		
Gate-Drain Charge	Q_{gd}			2.5		
Turn-On Delay Time	$t_{d(on)}$	$V_{DD} = 10V, V_{GS} = 4.5V,$ $R_L = 3\Omega, R_G = 3\Omega$		7		ns
Turn-On Rise Time	t_r			41		
Turn-Off Delay Time	$t_{d(off)}$			18		
Turn-Off Fall Time	t_f			12		
Source - Drain Diode Characteristics						
Diode Forward Voltage ³	V_{SD}	$V_{GS} = 0V, I_S = 1A$			1.2	V

Notes :

- 1.The maximum current rating is limited by package.
- 2.Pulse Test : Pulse Width $\leq 10\mu s$, duty cycle $\leq 1\%$.
- 3.Pulse Test : Pulse Width $\leq 300\mu s$, duty cycle $\leq 2\%$.
- 4.The power dissipation P_D is limited by $T_{J(MAX)} = 150^\circ\text{C}$.
- 5.Device mounted on 1in² FR-4 board with 2oz. Copper, in a still air environment with $T_A = 25^\circ\text{C}$.

Typical Characteristics



DFN2X2-6L Package Information


Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min.	Max.	Min.	Max.
A	1.950	2.050	0.077	0.081
B	1.950	2.050	0.077	0.081
C	0.450	0.550	0.018	0.022
L	0.200	0.300	0.008	0.012
L2	0.650TYP		0.026TYP	
L4	0.152TYP		0.006TYP	
a	0.900	1.000	0.035	0.039
b	1.550	1.650	0.061	0.065
l	0.300	0.400	0.012	0.016
k	0.000	0.050	0.000	0.002

Attention:

- GreenPower Electronics reserves the right to improve product design function and reliability without notice.
- Any and all semiconductor products have certain probability to fail or malfunction, which may result in personal injury, death or property damage. Customers are solely responsible for providing adequate safe measures when design their systems.
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